

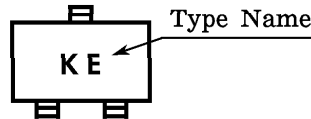
TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

# 2SK1062

HIGH SPEED SWITCHING APPLICATIONS  
 ANALOG SWITCHING APPLICATIONS  
 INTERFACE APPLICATIONS

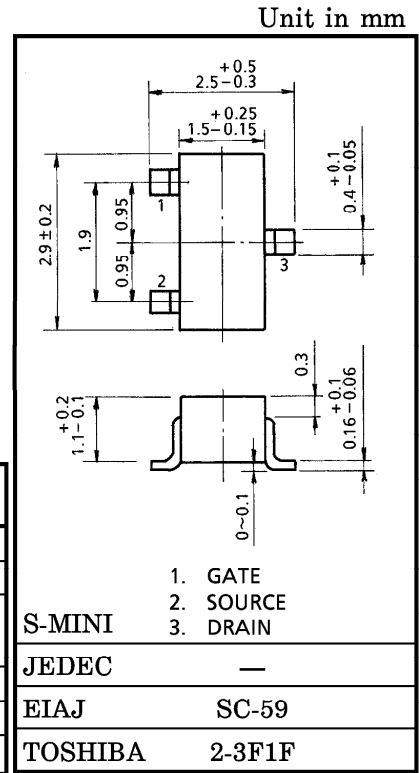
- Excellent Switching Time :  $t_{on} = 14\text{ns}$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 100\text{mS}$  (Min.) @  $I_D = 50\text{mA}$
- Low On Resistance :  $R_{DS(ON)} = 0.6\Omega$  (Typ.) @  $I_D = 50\text{mA}$
- Enhancement-Mode
- Complementary to 2SJ168.

Marking



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	DC	$I_D$	200
	Pulse	$I_{DP}$	800
Drain Power Dissipation (Ta = 25°C)	$P_D$	200	mW
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C



Weight : 0.012g

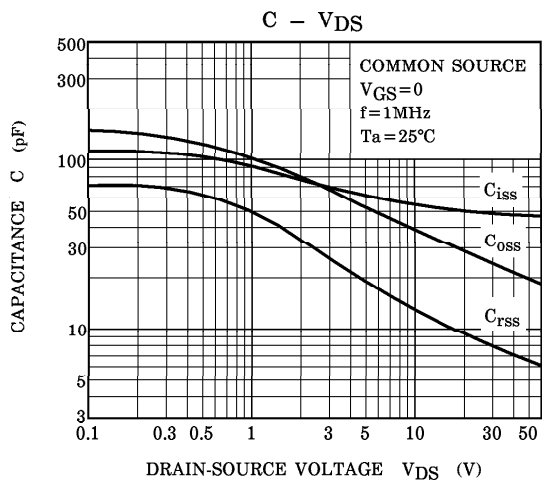
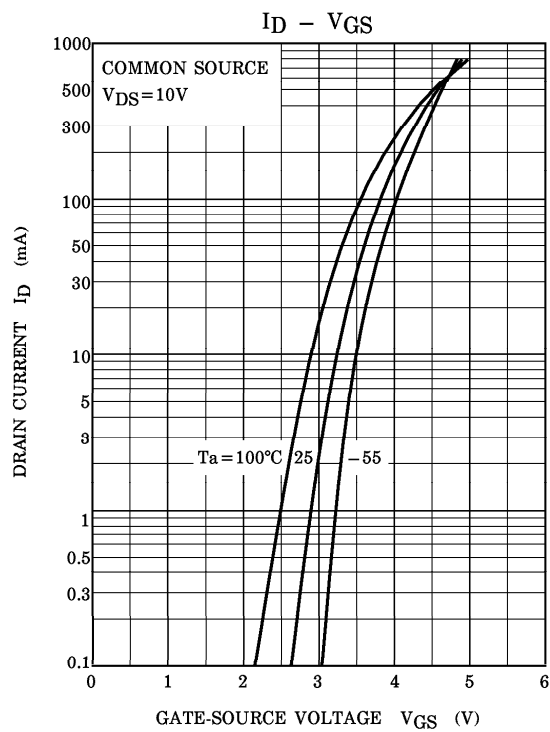
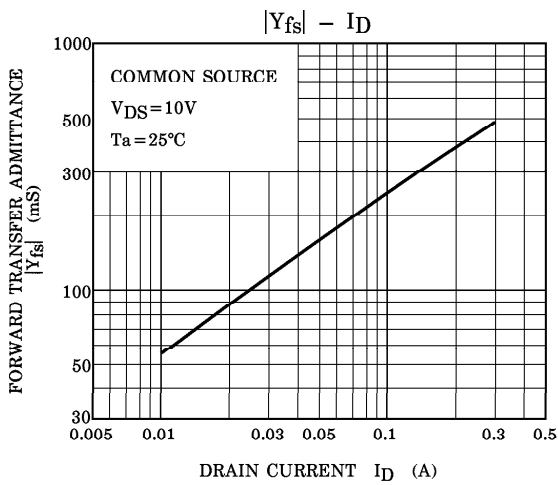
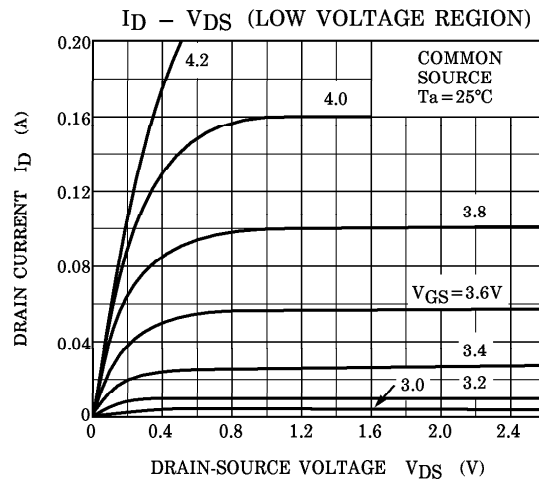
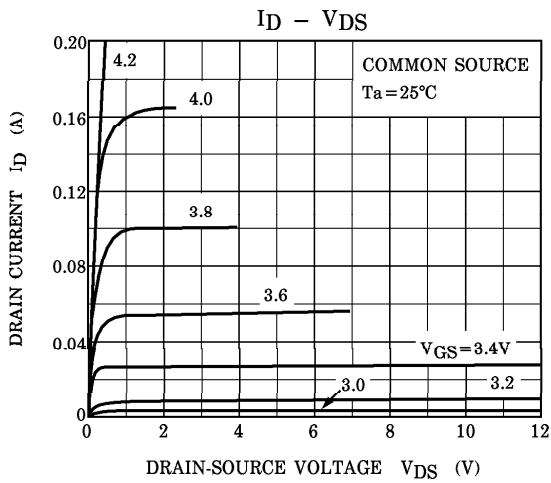
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \pm 10\text{V}, V_{DS} = 0$	—	—	$\pm 100$	nA
Drain Cut-off Current	$I_{DSS}$	$V_{DS} = 60\text{V}, V_{GS} = 0$	—	—	10	$\mu\text{A}$
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	60	—	—	V
Gate Threshold Voltage	$V_{th}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	2	—	3.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 50\text{mA}$	100	—	—	mS
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D = 50\text{mA}, V_{GS} = 10\text{V}$	—	0.6	1.0	$\Omega$
Drain-Source ON Voltage	$V_{DS(ON)}$	$I_D = 50\text{mA}, V_{GS} = 10\text{V}$	—	30	50	mV
Input Capacitance	$C_{iss}$	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$	—	55	65	pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$	—	13	18	pF
Output Capacitance	$C_{oss}$	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$	—	40	50	pF
Switching Time	Rise Time	$t_r$	—	8	—	ns
	Turn-on Time	$t_{on}$	—	14	—	
	Fall Time	$t_f$	—	35	—	
	Turn-off Time	$t_{off}$	—	75	—	

This transistor is the electrostatic sensitive device. Please handle with caution.

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